NPN Triple Diffused Planar Silicon Transistor



2SC5967

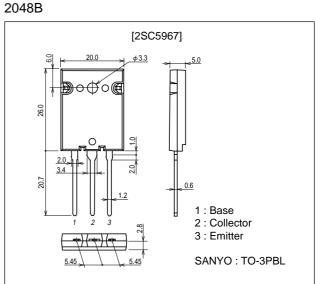
Ultrahigh-Definition CRT Display Horizontal Deflection Output Applications

Features

- High-speed.
- High breakdown voltage (VCBO=1700V).
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta= $25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		1700	V
Collector-to-Emitter Voltage	VCEO		800	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	IC		20	А
Collector Current (Pulse)	ICP		40	А
Collector Dissipation	De		3.5	W
	PC	Tc=25°C	180	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =800V, I _E =0			10	μΑ
	ICES	V _{CE} =1700V, R _{BE} =0			1.0	mA
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=10mA, RBE=∞	800			V
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0			1.0	mA

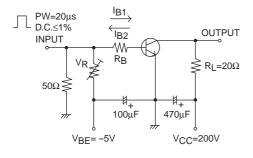
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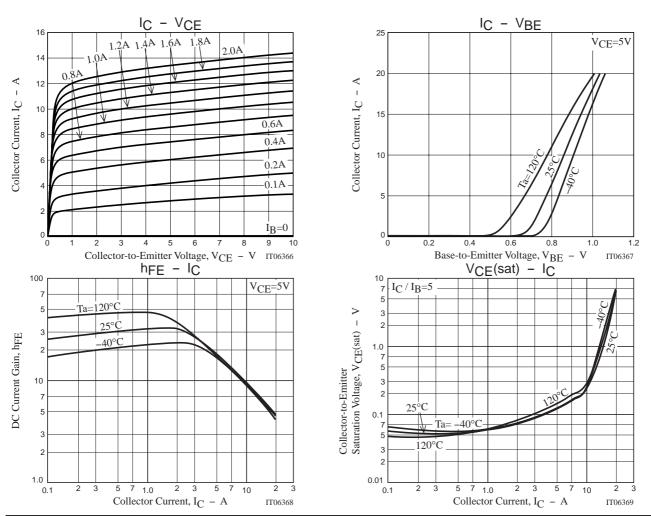
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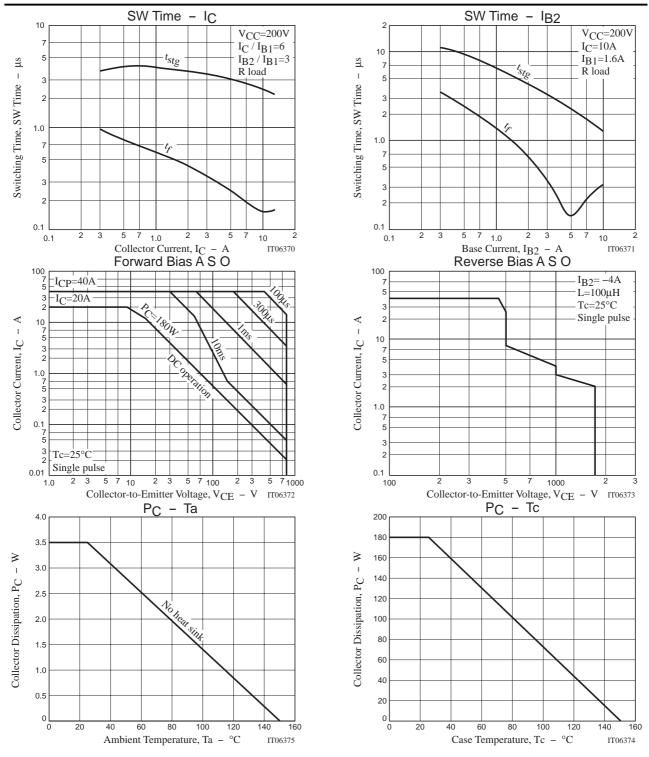
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
DC Current Gain	hFE1	V _{CE} =5V, I _C =1A	15			
	hFE2	V _{CE} =5V, I _C =15A	4		7	
Collectoe-to-Emitter Saturation Voltage	VCE(sat)	IC=13.5A, IB=3.4A			3	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	IC=13.5A, IB=3.4A			1.5	V
Storage Time	tstg	I _C =10A, I _{B1} =1.6A, I _{B2} =-5.0A			3.0	μs
Fall Time	tf	IC=10A, IB1=1.6A, IB2=-5.0A			0.2	μs

Switching Time Test Circuit







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